FAIRCHILD SEMICONDUCTOR®

March 2013

FDP26N40

N-Channel UniFET™ MOSFET

400 V, 26 A, 160 mΩ

Features

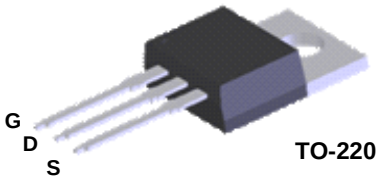
- $R_{DS(on)}$ = 130 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 13 A
- Low Gate Charge (Typ. 48 nC)
- Low C_{rss} (Typ. 30 pF)
- 100% Avalanche Tested
- RoHS Compliant

Applications

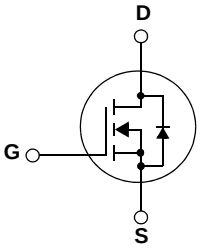
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFET™ MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter			FDP26N40	Unit
V_{DSS}	Drain to Source Voltage			400	V
V_{GSS}	Gate to Source Voltage			±30	V
I_D	Drain Current	- Continuous (T_C = 25°C)		26	A
		- Continuous (T_C = 100°C)		15.6	
I_{DM}	Drain Current	- Pulsed	(Note 1)	104	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	1352	mJ
I_{AR}	Avalanche Current		(Note 1)	26	A
E_{AR}	Repetitive Avalanche Energy		(Note 1)	26.5	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C)		265	W
		- Derate above 25°C		2.0	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter	FDP26N40	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.5	°C/W
$R_{\theta CS}$	Thermal Resistance, Case to Sink, Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information $T_C = 25^oC$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP26N40	FDP26N40	TO-220	-	-	50

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu A$, $V_{GS} = 0V$, $T_J = 25^oC$	400	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to 25^oC	-	0.5	-	$V/^oC$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 400V$, $V_{GS} = 0V$	-	-	1	μA
		$V_{DS} = 320V$, $T_C = 125^oC$	-	-	10	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm30V$, $V_{DS} = 0V$	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu A$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10V$, $I_D = 13A$	-	0.13	0.16	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20V$, $I_D = 13A$	-	25.5	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, f = 1MHz	-	2400	3185	pF
C_{oss}	Output Capacitance		-	390	520	pF
C_{rss}	Reverse Transfer Capacitance		-	30	45	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 320V$, $I_D = 26A$, $V_{GS} = 10V$ (Note 4)	-	48	60	nC
Q_{gs}	Gate to Source Gate Charge		-	15	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	20	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 200V$, $I_D = 26A$, $R_G = 25\Omega$ (Note 4)	-	45	100	ns
t_r	Turn-On Rise Time		-	100	210	ns
$t_{d(off)}$	Turn-Off Delay Time		-	115	240	ns
t_f	Turn-Off Fall Time		-	66	140	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	26	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	104	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V$, $I_{SD} = 26A$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0V$, $I_{SD} = 26A$, $dI_F/dt = 100A/\mu s$	-	406	-	ns
Q_{rr}	Reverse Recovery Charge		-	5.17	-	μC

Notes:
1: Repetitive Rating: Pulse width limited by maximum junction temperature
2: L = 4mH, $I_{AS} = 26A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25°C$
3: $I_{SD} \le 26A$, $di/dt \le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25°C$
4: Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

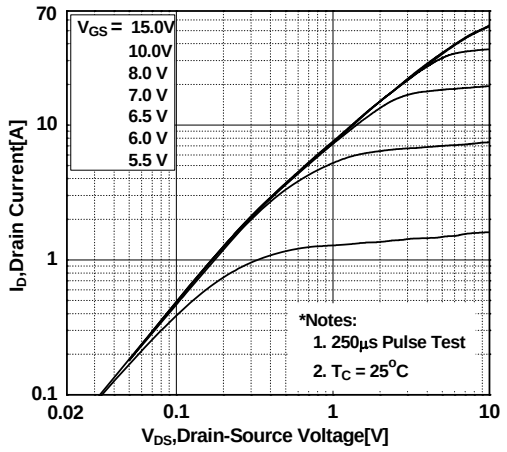


Figure 2. Transfer Characteristics

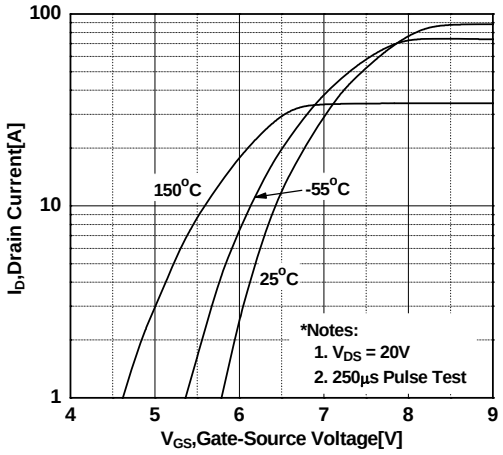


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

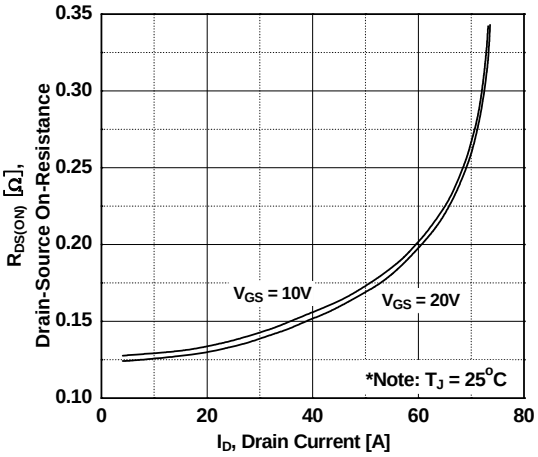


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

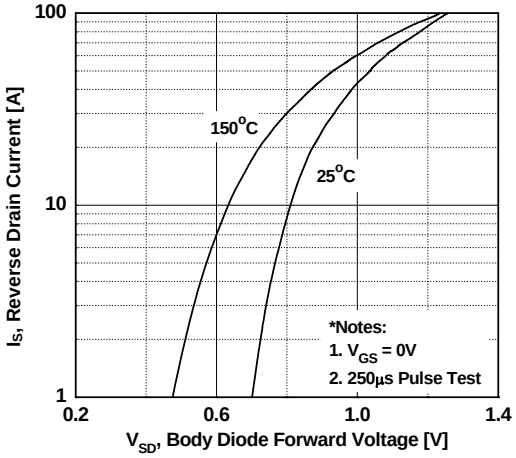


Figure 5. Capacitance Characteristics

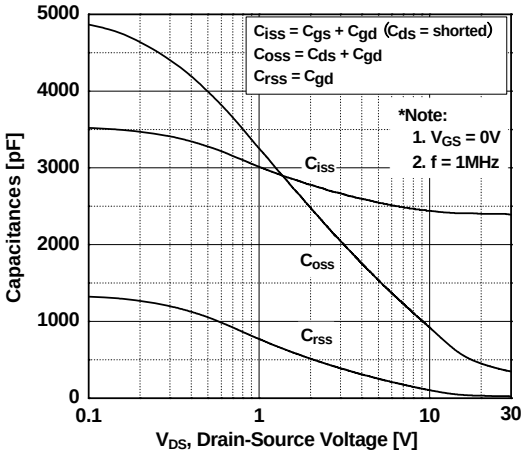
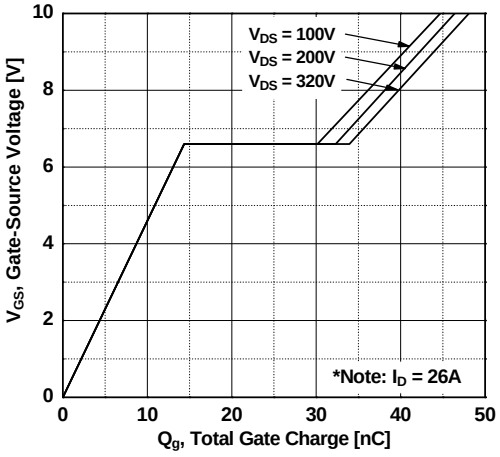


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

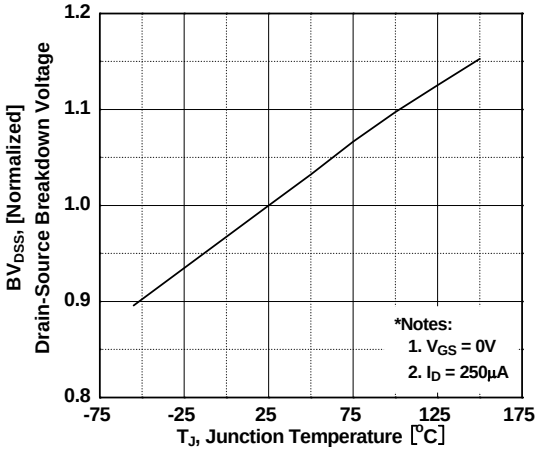


Figure 8. On-Resistance Variation vs. Temperature

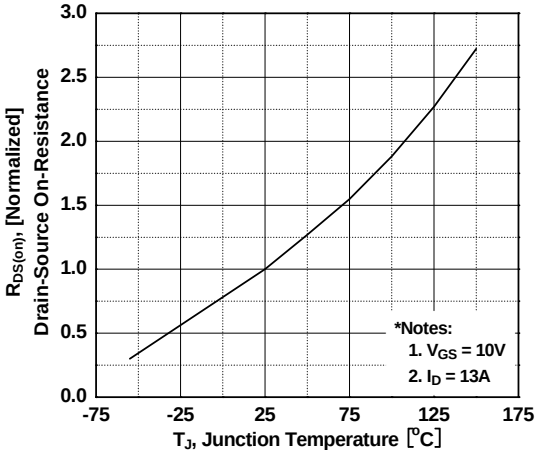


Figure 9. Maximum Safe Operating Area - FDP26N40

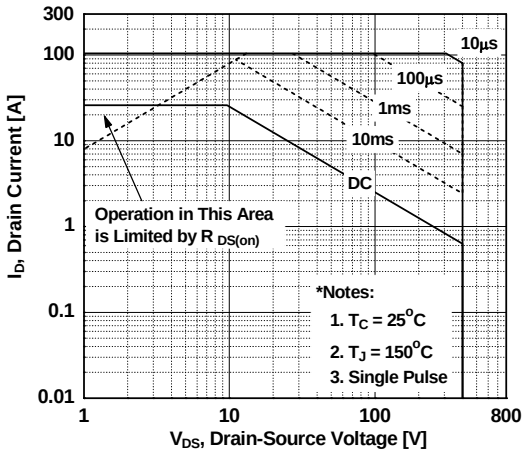


Figure 10. Maximum Safe Operating Area

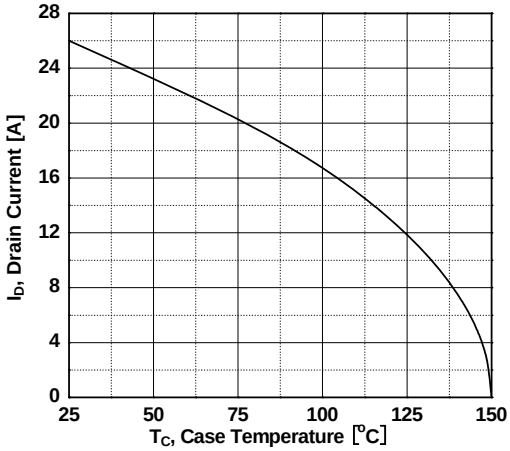
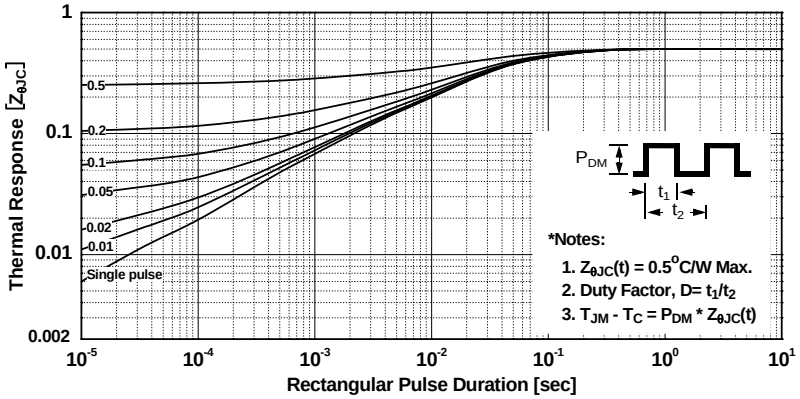
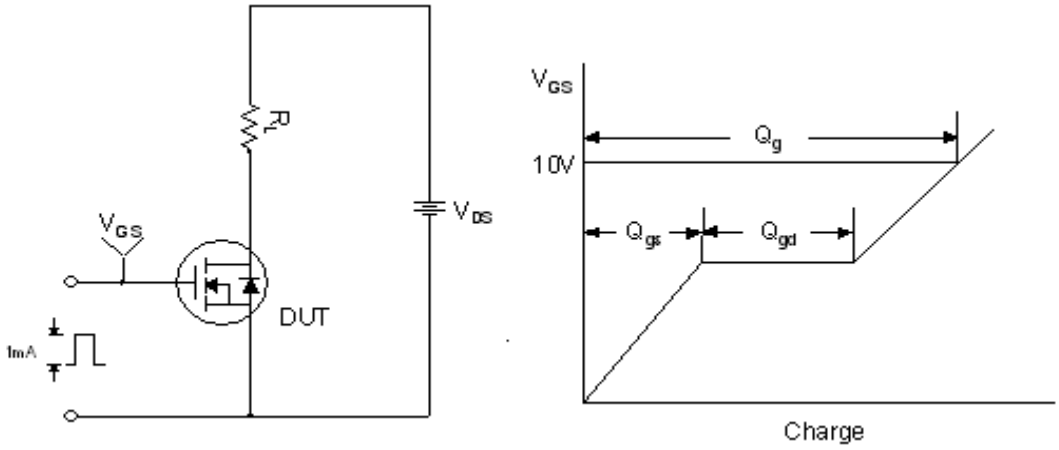


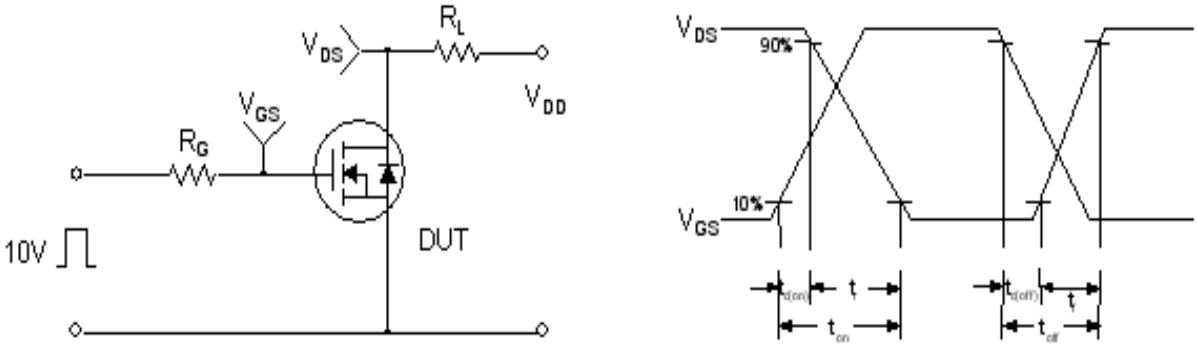
Figure 11. Transient Thermal Response Curve - FDP26N40



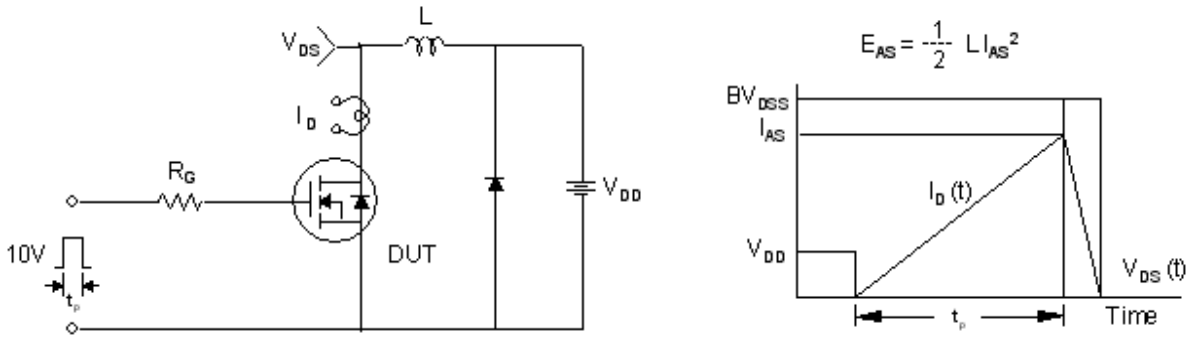
Gate Charge Test Circuit & Waveform



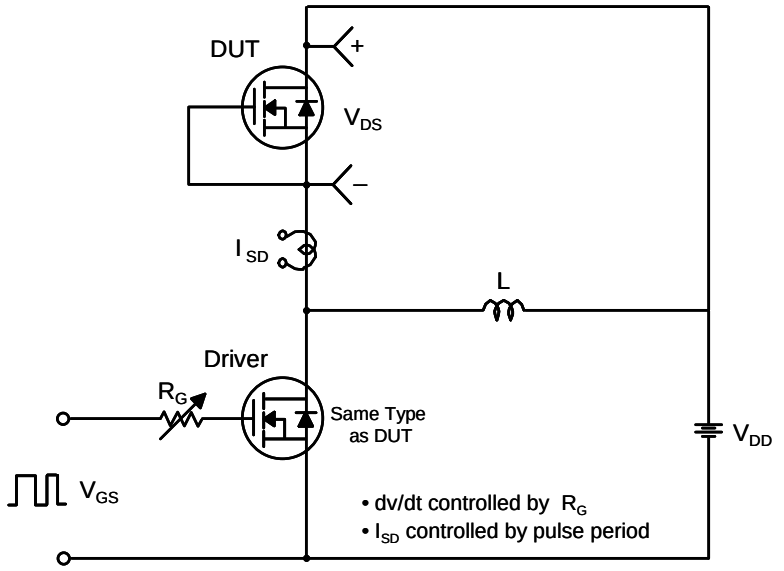
Resistive Switching Test Circuit & Waveforms

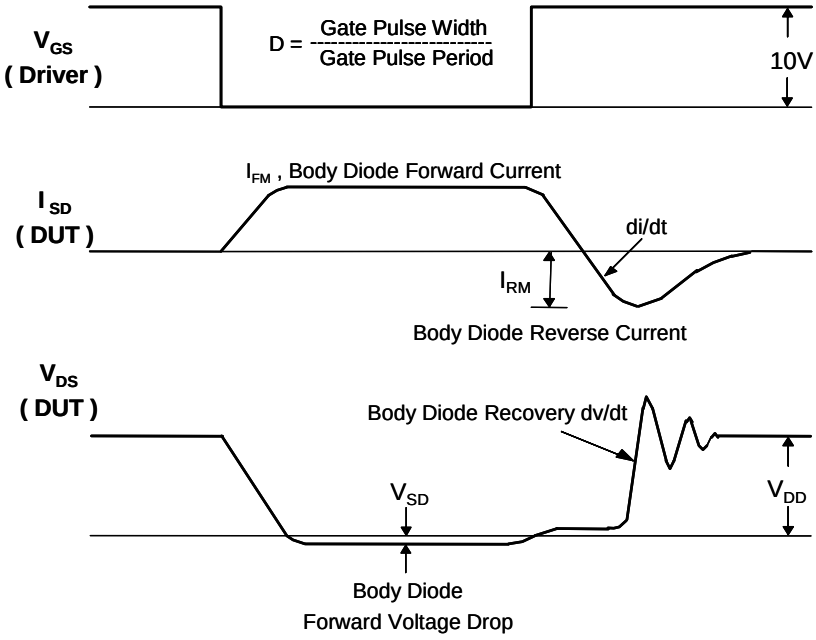


Unclamped Inductive Switching Test Circuit & Waveforms



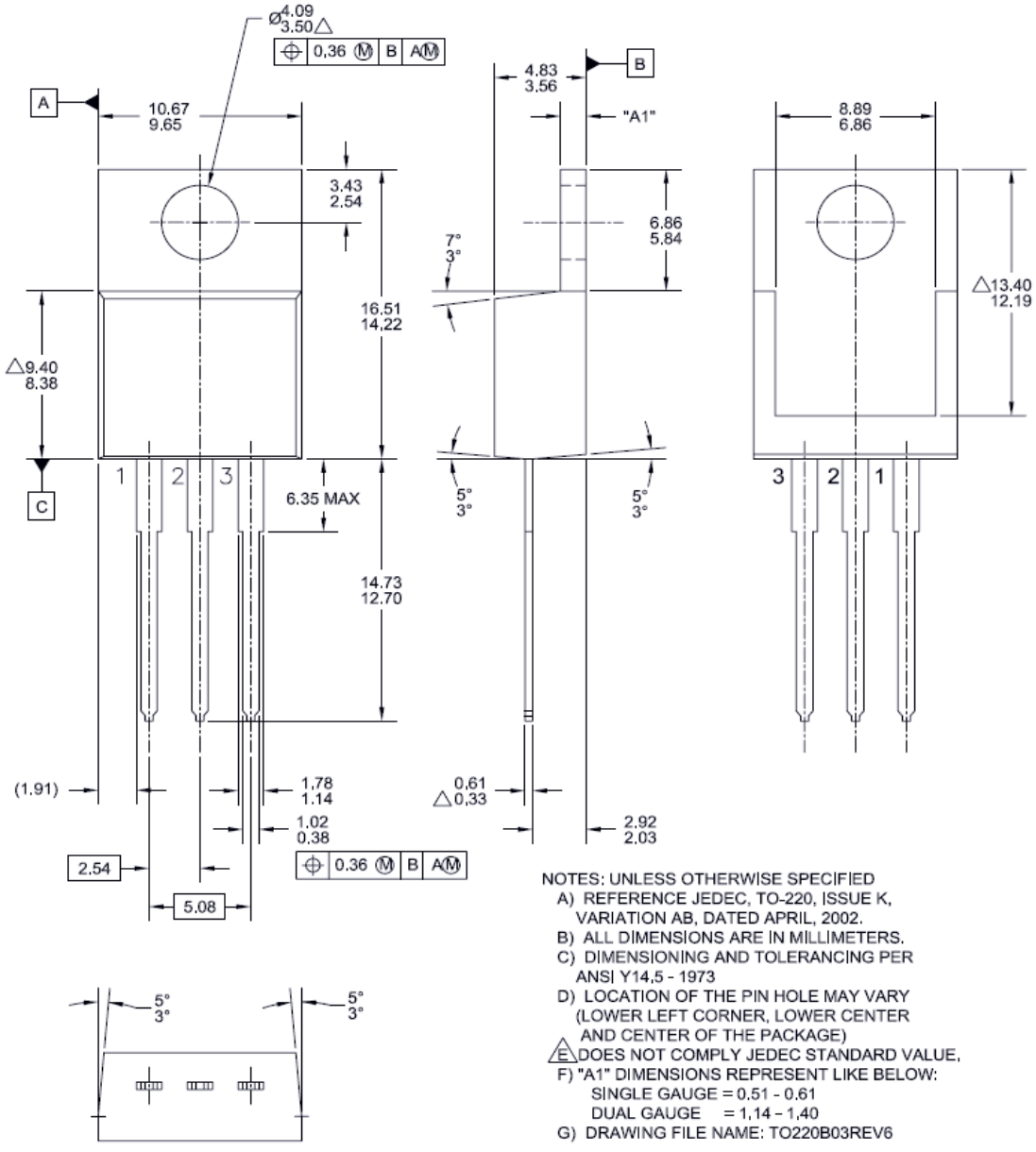
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

TO-220B03



NOTES: UNLESS OTHERWISE SPECIFIED
A) REFERENCE JEDEC, TO-220, ISSUE K, VARIATION AB, DATED APRIL, 2002.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5 - 1973
D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
△E DOES NOT COMPLY JEDEC STANDARD VALUE,
F) "A1" DIMENSIONS REPRESENT LIKE BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1,14 – 1,40
G) DRAWING FILE NAME: TO220B03REV6

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